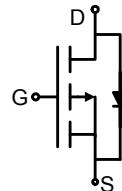


## P-Channel Enhancement Mode Power MOSFET

### Description

The PT HEÚEGS uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.



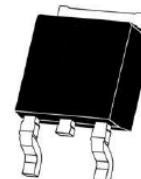
Schematic diagram

### General Features

- $V_{DS} = -20V, I_D = -30A$
- $R_{DS(ON)} < 27m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 39m\Omega @ V_{GS}=-2.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface Mount Package



Marking and pin Assignment



TO-252-2L top view

### Application

- Motor drive
- Load switch
- Power management

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HMHEÚEGS	PT HEÚEGS	VUÉG GEÉS	Ø330mm	12mm	2500 units

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	-30	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	-90	A
Maximum Power Dissipation	$P_D$	3.0	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	42	$^\circ C/W$
---	-----------------	----	--------------

### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.6	-0.8	-1.4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6.5A	-	21	27	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-5A	-	29	39	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =3A	-	10	-	S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C <sub>oss</sub>		-	450	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	300	-	PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, ID=-1A, V <sub>GS</sub> =-4.5V, R <sub>GEN</sub> =6Ω	-	25	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	30	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	70	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	50	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-6.5A, V <sub>GS</sub> =-4.5V	-	17	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	4.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-30A	-	-	-1.2	V

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

### Typical Electrical and Thermal Characteristics

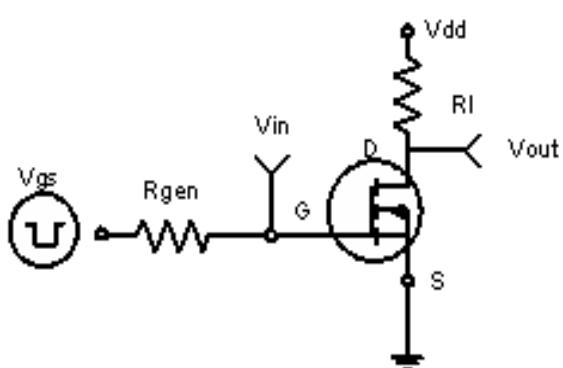


Figure 1 Switching Test Circuit

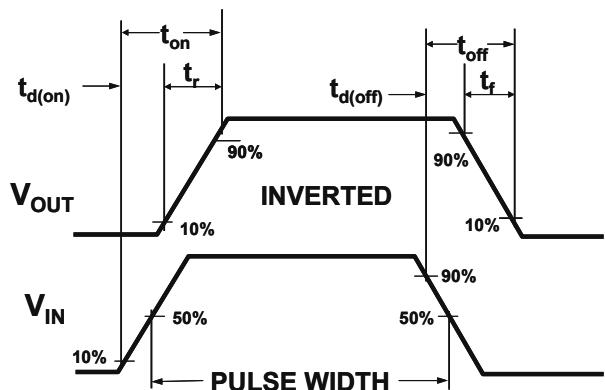


Figure 2 Switching Waveforms

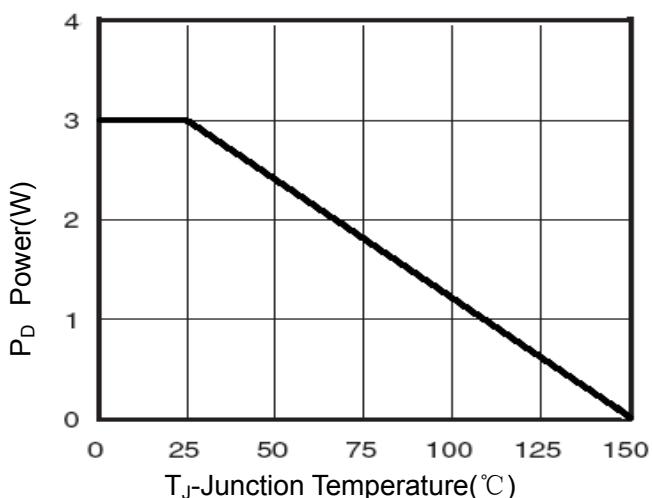


Figure 3 Power Dissipation

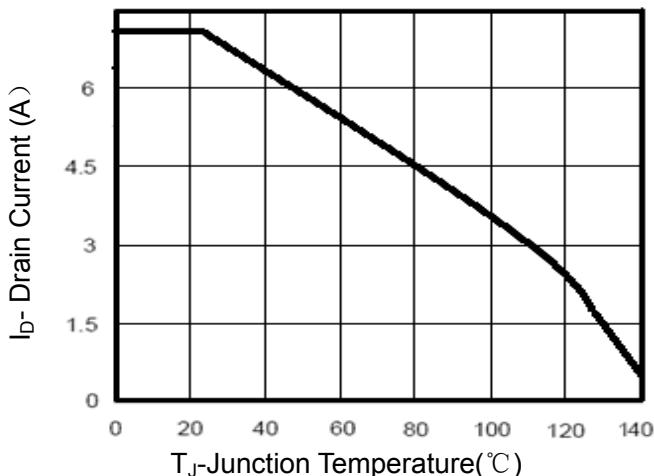


Figure 4 Drain Current

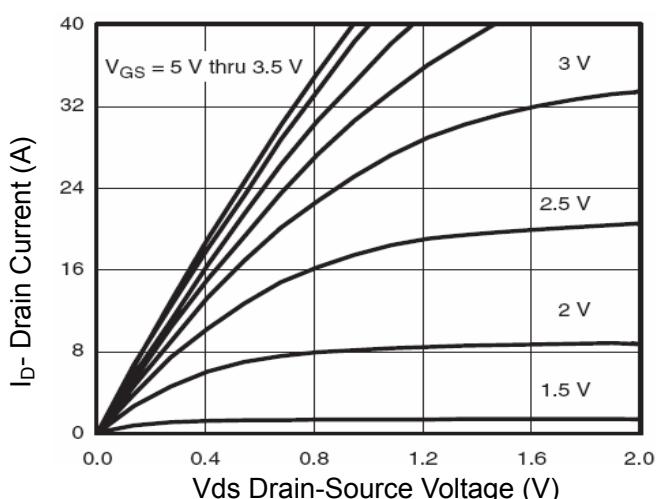


Figure 5 Output Characteristics

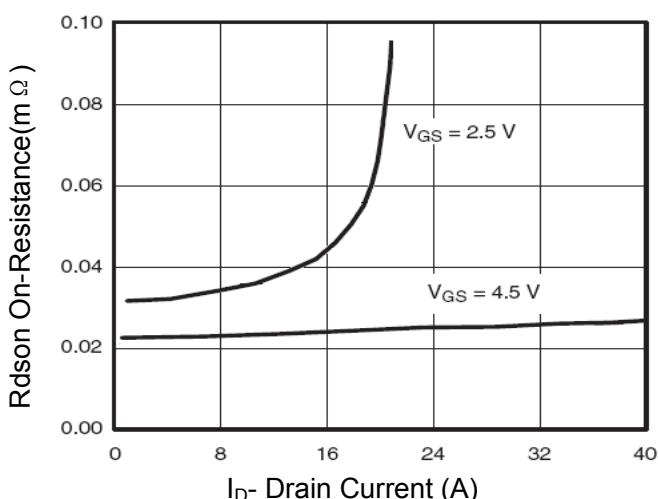
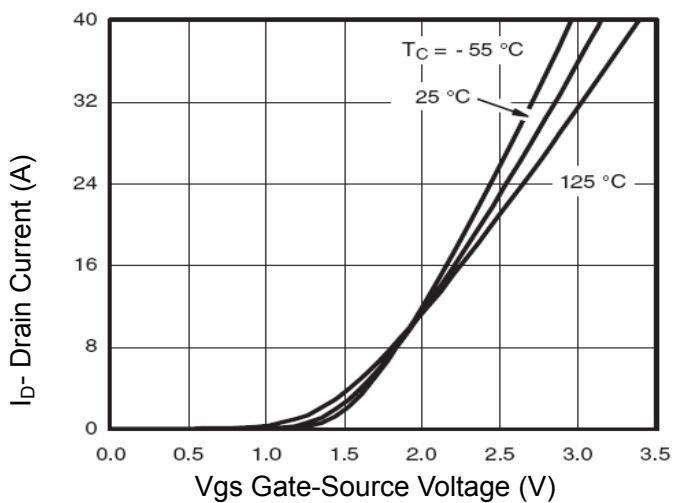
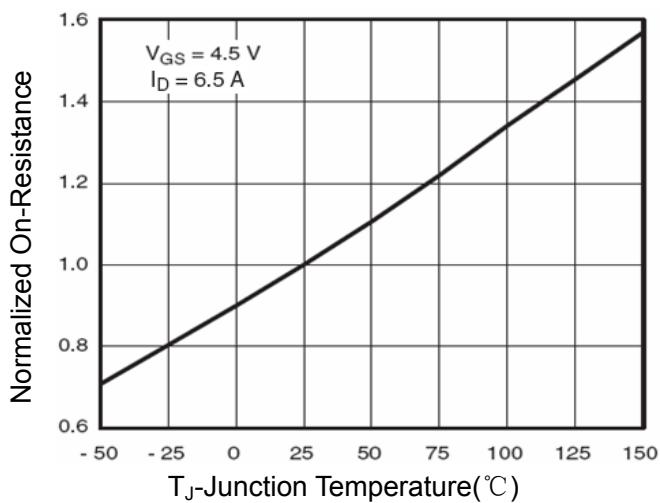


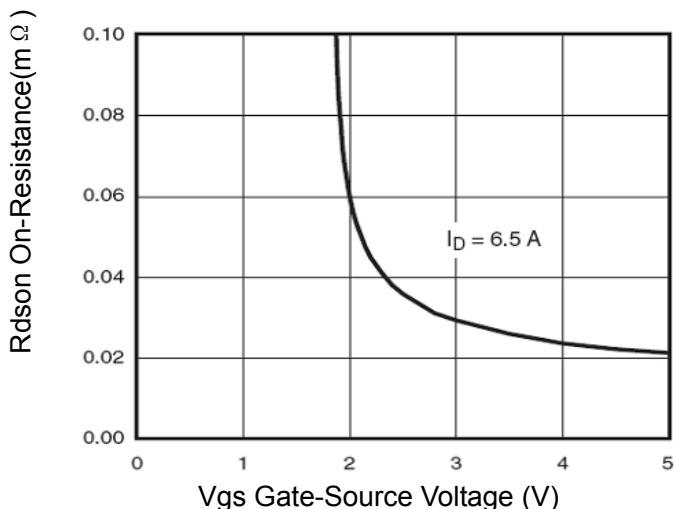
Figure 6 Drain-Source On-Resistance



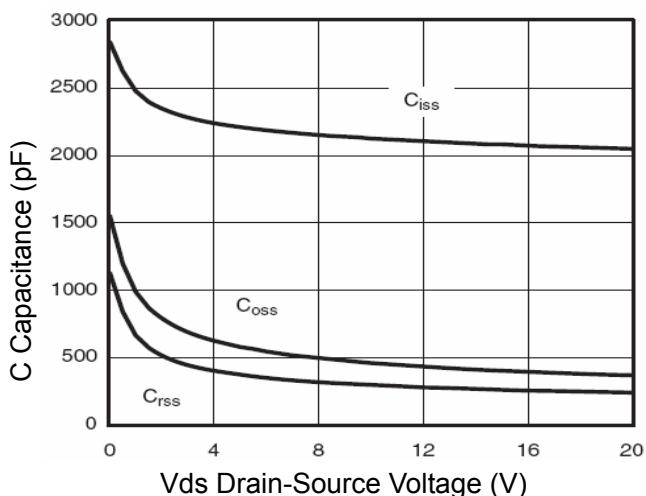
**Figure 7 Transfer Characteristics**



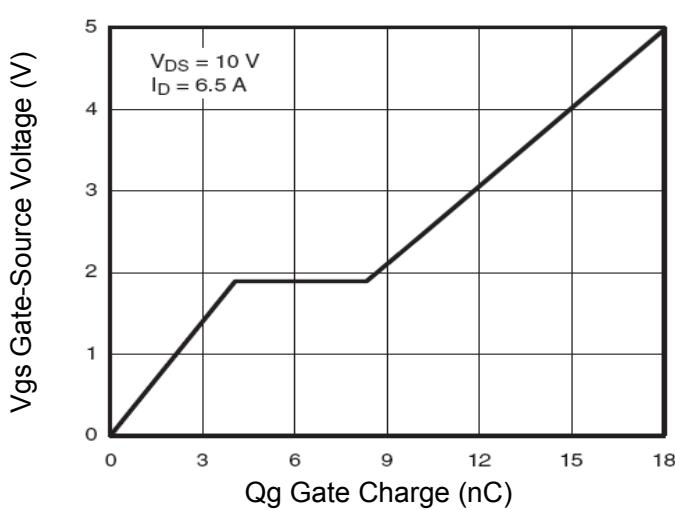
**Figure 8 Drain-Source On-Resistance**



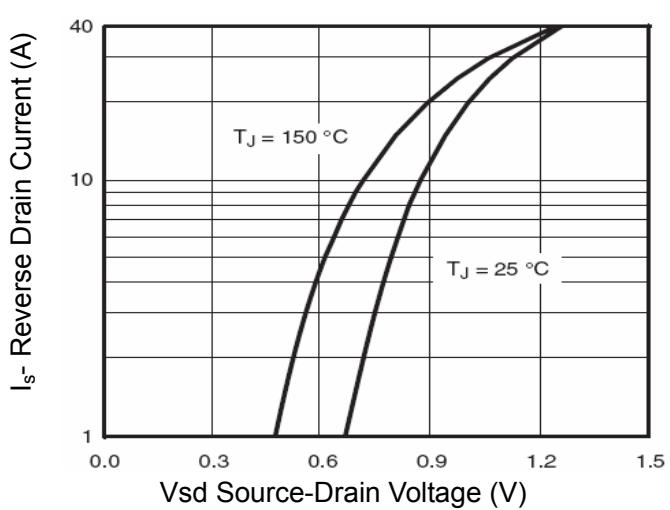
**Figure 9  $R_{DS(on)}$  vs  $V_{GS}$**



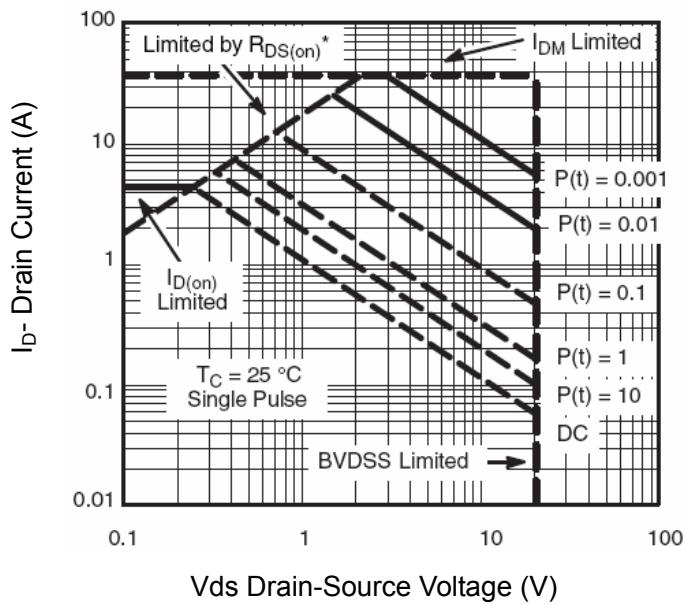
**Figure 10 Capacitance vs  $V_{DS}$**



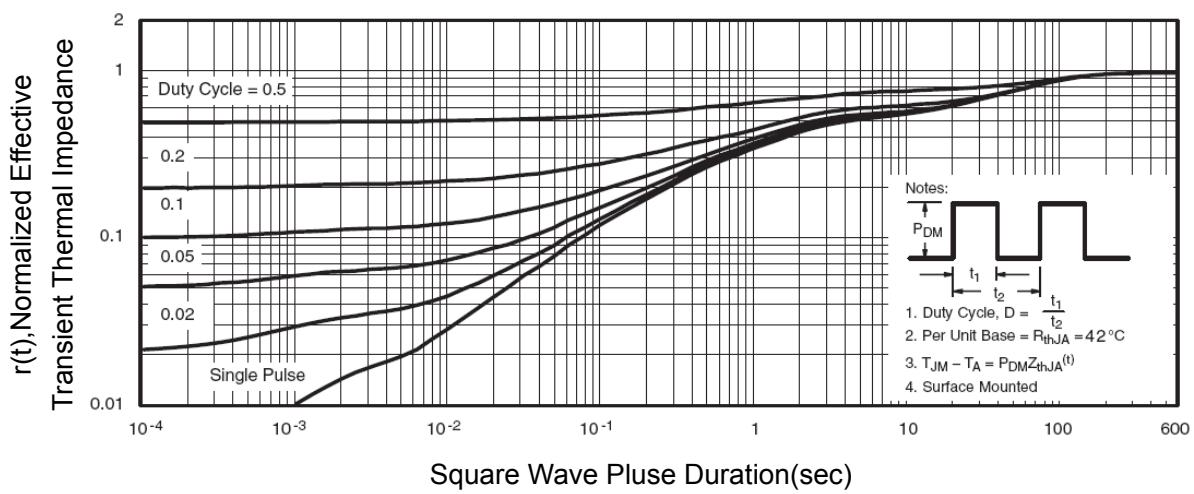
**Figure 11 Gate Charge**



**Figure 12 Source-Drain Diode Forward**

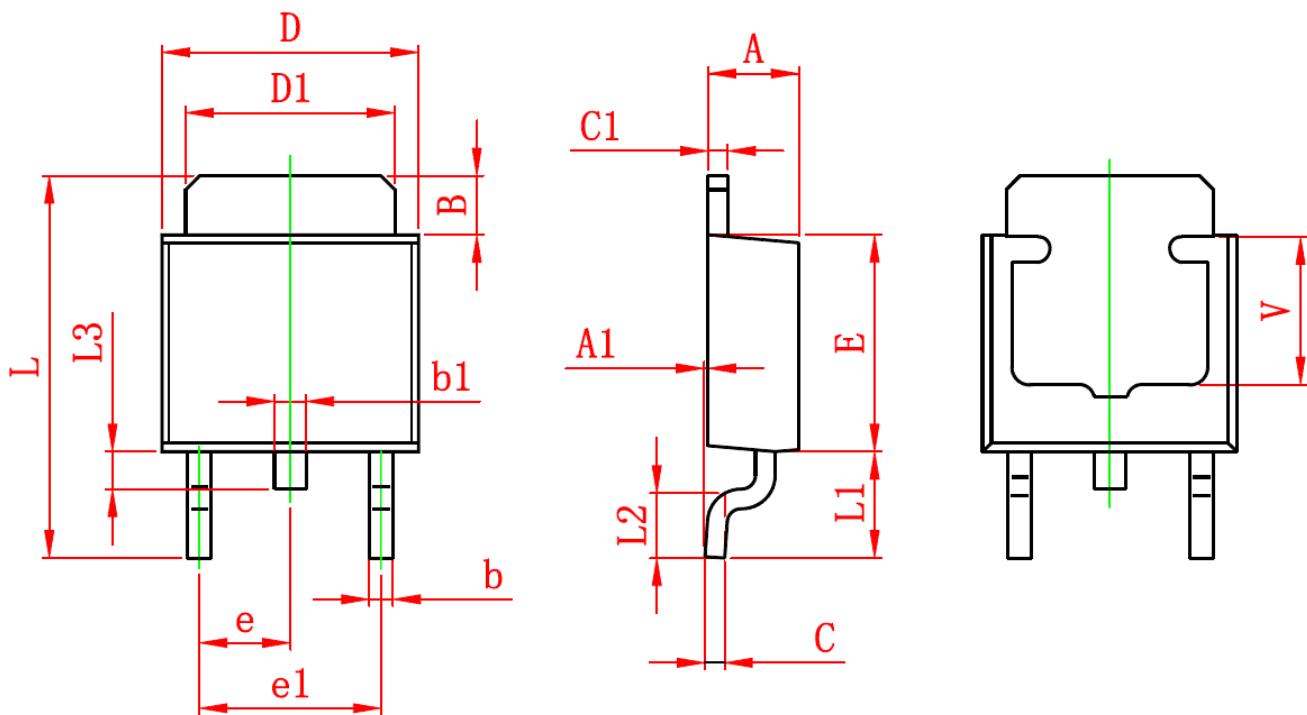


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

**TO-252-2L PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	